

# 24-30GHz Integrated Down Converter

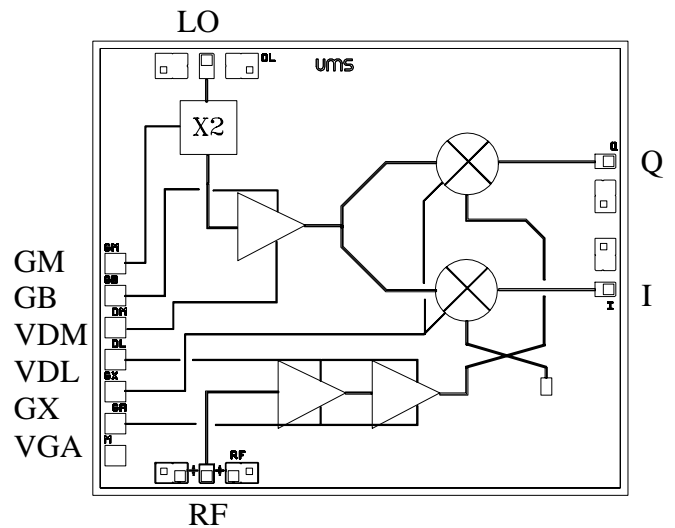
## GaAs Monolithic Microwave IC

*preliminary*

### Description

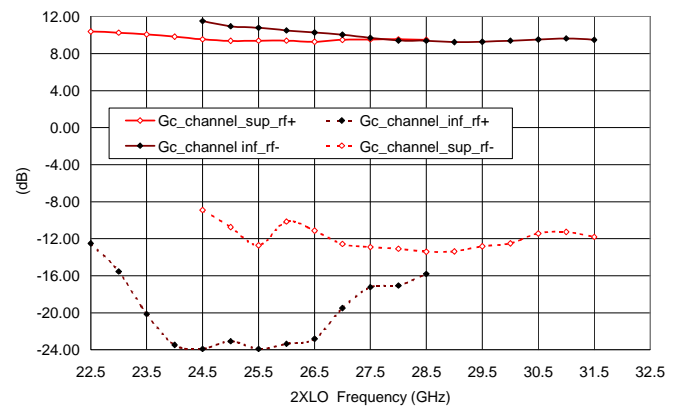
The CHR2295 is a multifunction chip which integrates a LO time two multiplier, a balanced cold FET mixer, and a RF LNA. It is designed for a wide range of applications, typically commercial communication systems. The backside of the chip is both RF and DC grounds. This helps simplify the assembly process.

The circuit is manufactured with a PM-HEMT process, 0.25 $\mu$ m gate length, via holes through the substrate, air bridges and electron beam gate lithography. It is available in chip form.



### Main Features

- Broadband performances : 24-30GHz
- 11 dB conversion gain
- 3.5.0dB noise figure
- 10dBm LO input power
- -10dBm RF input power (1dB gain comp.)
- Low DC power consumption, 120mA@3.5V
- Chip size : 2.49 X 1.97 X 0.10 mm



Conversion Gain & Image suppression @ IF=1.5GHz  
(including test board losses)

### Main Characteristics

Tamb. = 25°C

	Parameter	Min	Typ	Max	Unit
F <sub>RF</sub>	RF frequency range	24		30	GHz
F <sub>LO</sub>	LO frequency range	12		15	GHz
F <sub>IF</sub>	IF frequency range	0.25		1.5	GHz
G <sub>c</sub>	Conversion gain		11		dB

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !

Ref. : DSCHR22951201 -20-July-01

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Specifications subject to change without notice

## Electrical Characteristics for Broadband Operation

T<sub>amb</sub> = +25°C, V<sub>d</sub> = 3.5V

Symbol	Parameter	Min	Typ	Max	Unit
F <sub>RF</sub>	RF frequency range	24		30	GHz
F <sub>LO</sub>	LO frequency range	12		15	GHz
F <sub>IF</sub>	IF frequency range	0.25		1.5	GHz
G <sub>c</sub>	Conversion gain (1)		11		dB
NF	Noise Figure		3.5		dB
P <sub>LO</sub>	LO Input power		+10		dBm
Img Sup	Image Suppression		17		dBc
P1dB	Input power at 1dB gain compression		-10		dBm
LO VSWR	Input LO VSWR (1)		2.0:1		
RF VSWR	Input RF VSWR (1)		3.0:1		
I <sub>d</sub>	Bias current (2)		120		mA

(1) On Wafer measurements

(2) Current source biasing network is recommended. Optimum performances for I<sub>dm</sub>= 50mA and I<sub>dl</sub>= 70mA

## Absolute Maximum Ratings

T<sub>amb.</sub> = 25°C (1)

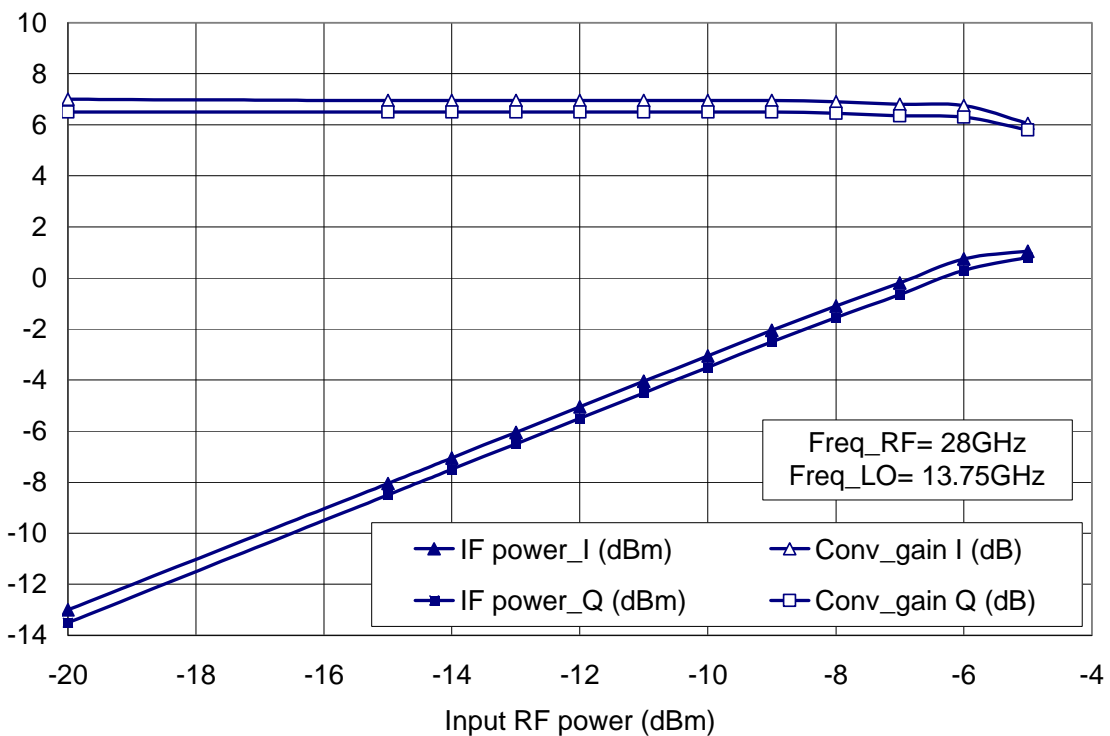
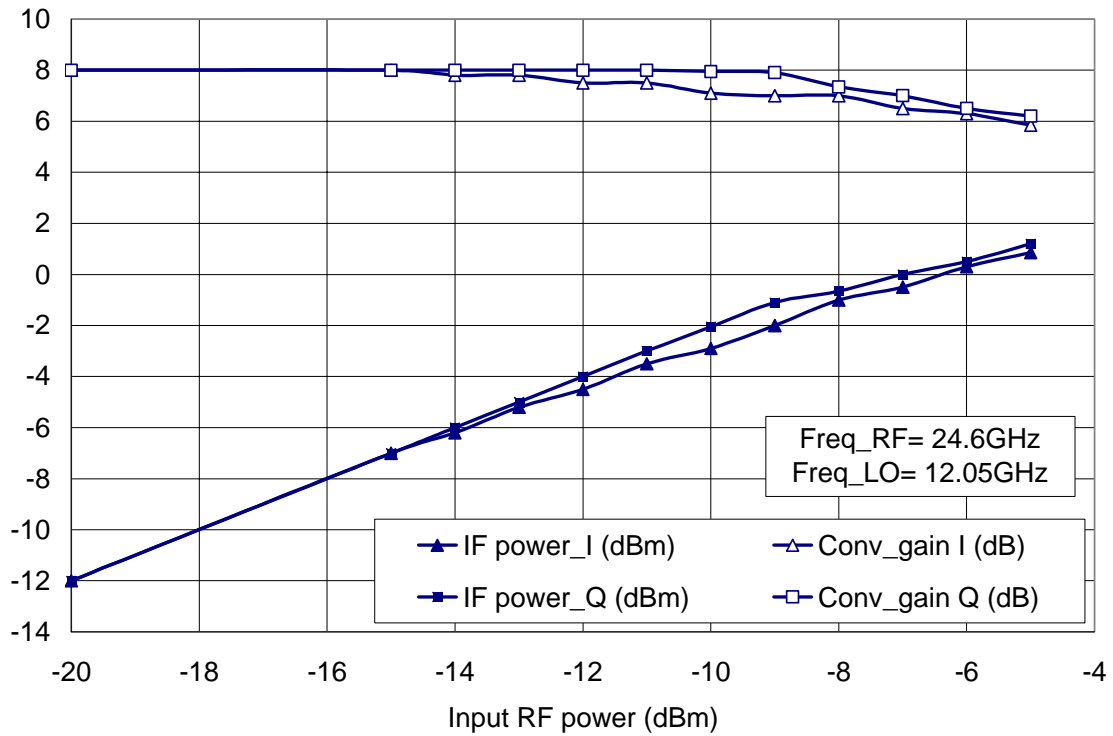
Symbol	Parameter	Values	Unit
V <sub>d</sub>	Drain bias voltage	4.0	V
I <sub>d</sub>	Drain bias current	200	mA
V <sub>g</sub>	Gate bias voltage	-2.0 to +0.4	V
P <sub>in</sub>	Maximum peak input power overdrive (2)	+15	dBm
T <sub>a</sub>	Operating temperature range	-40 to +85	°C
T <sub>stg</sub>	Storage temperature range	-55 to +155	°C

(1) Operation of this device above anyone of these parameters may cause permanent damage.

(2) Duration < 1s.

## Typical On-wafer Measurements

Bias Conditions :  $V_{dm} = V_{dl} = 3.5\text{V}$ ,  $V_{gm} = -0.9\text{V}$ ,  $V_{gb} = -0.3\text{V}$ ,  $V_{gx} = -0.7\text{V}$ ,  $V_{ga} = -0.2\text{V}$

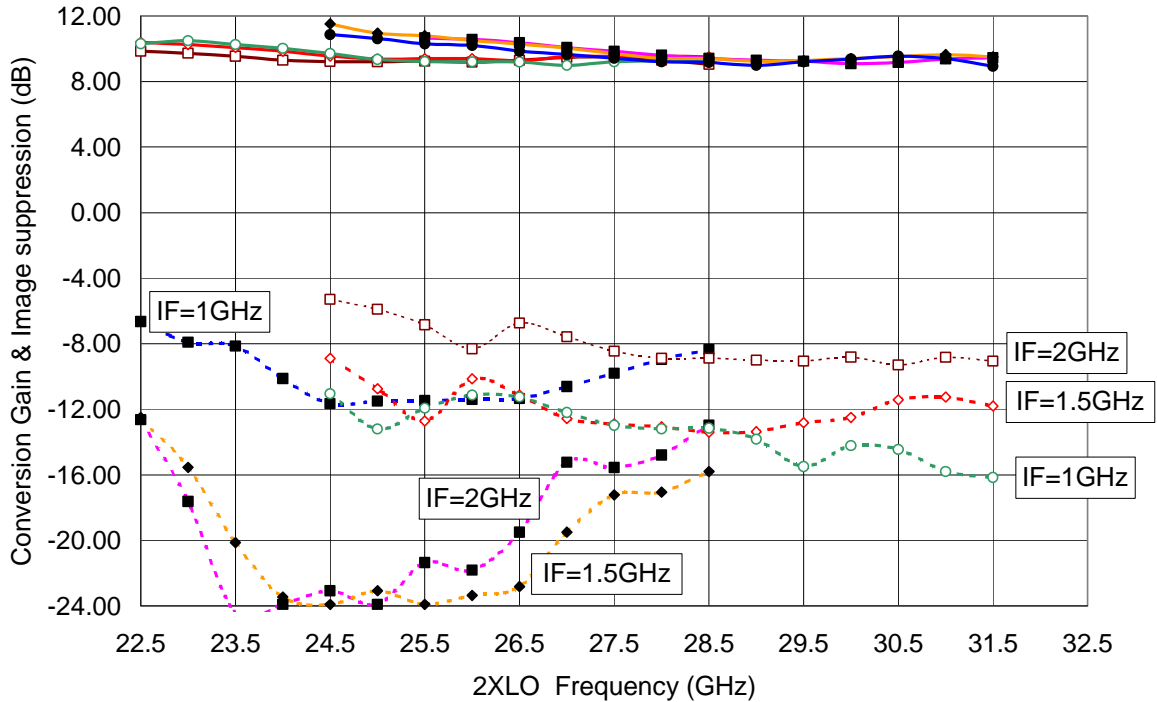


### Input RF compression by channel

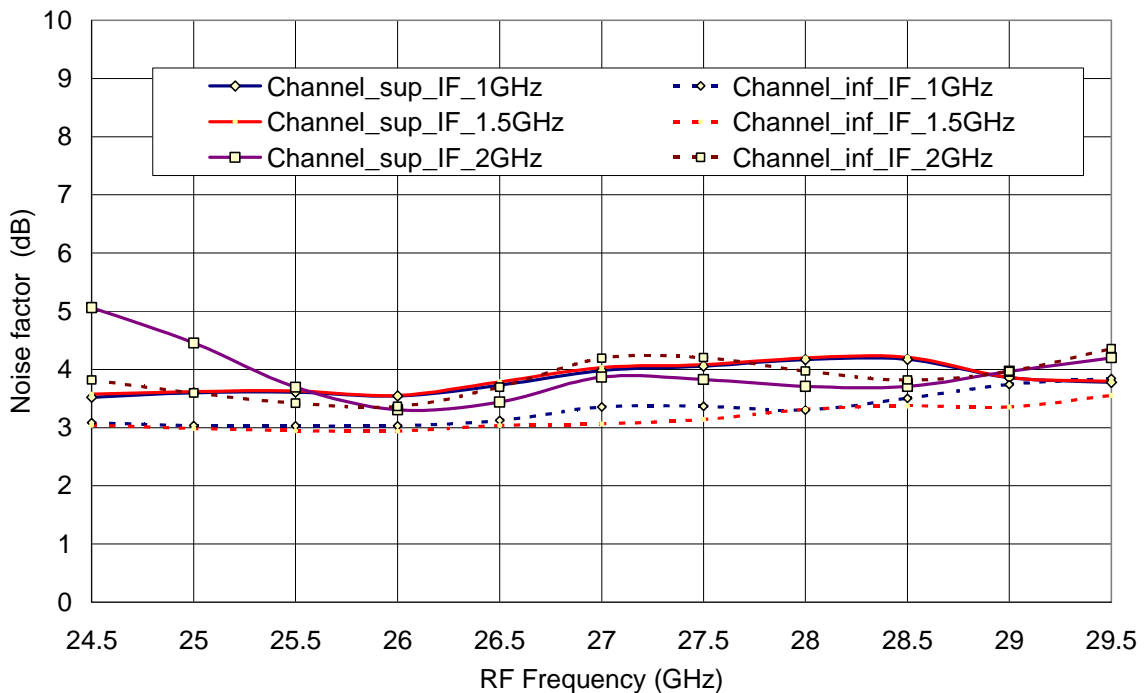
## Typical On-board Measurements

Bias Conditions :  $V_{dm} = V_{dl} = 3.5\text{ V}$ ,  $V_{gm} = V_{gx} = -0.9\text{ V}$ ,  $V_{gb} = V_{ga} = -0.3\text{ V}$

All these measurements include the losses from the test board (about 1dB on the conversion gain and 0.5dB on the noise figure).

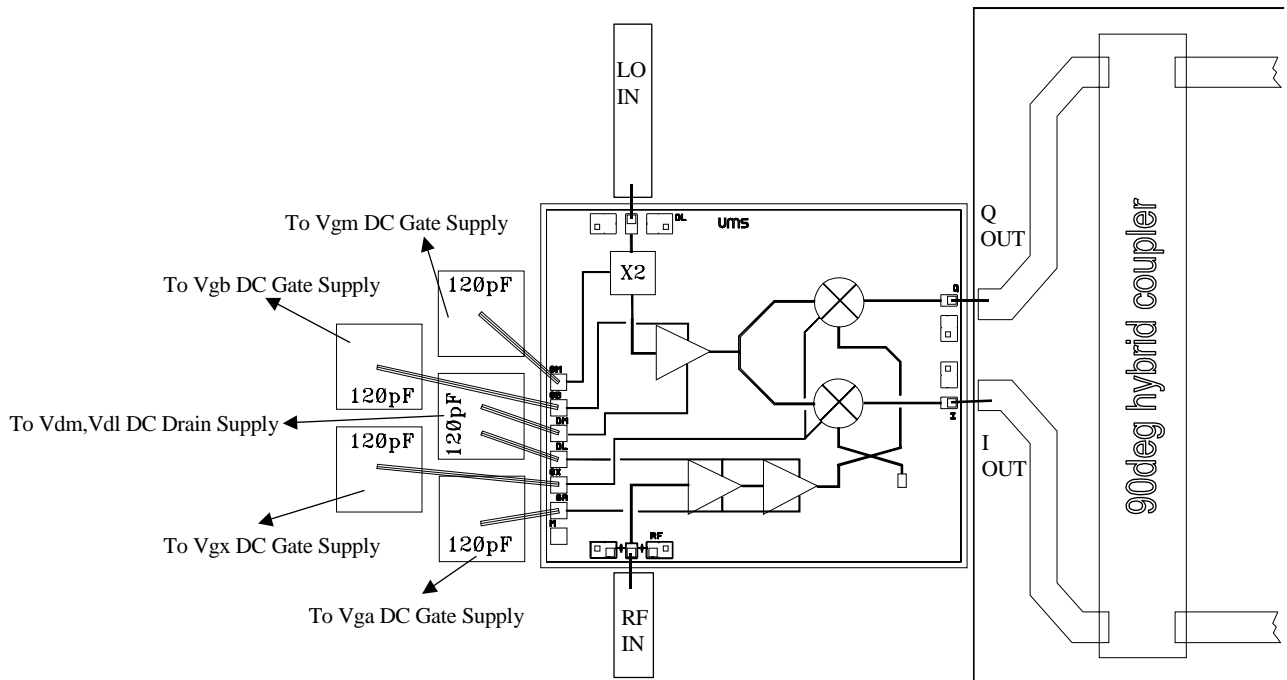


**Conversion gain & Image suppression versus IF frequency**

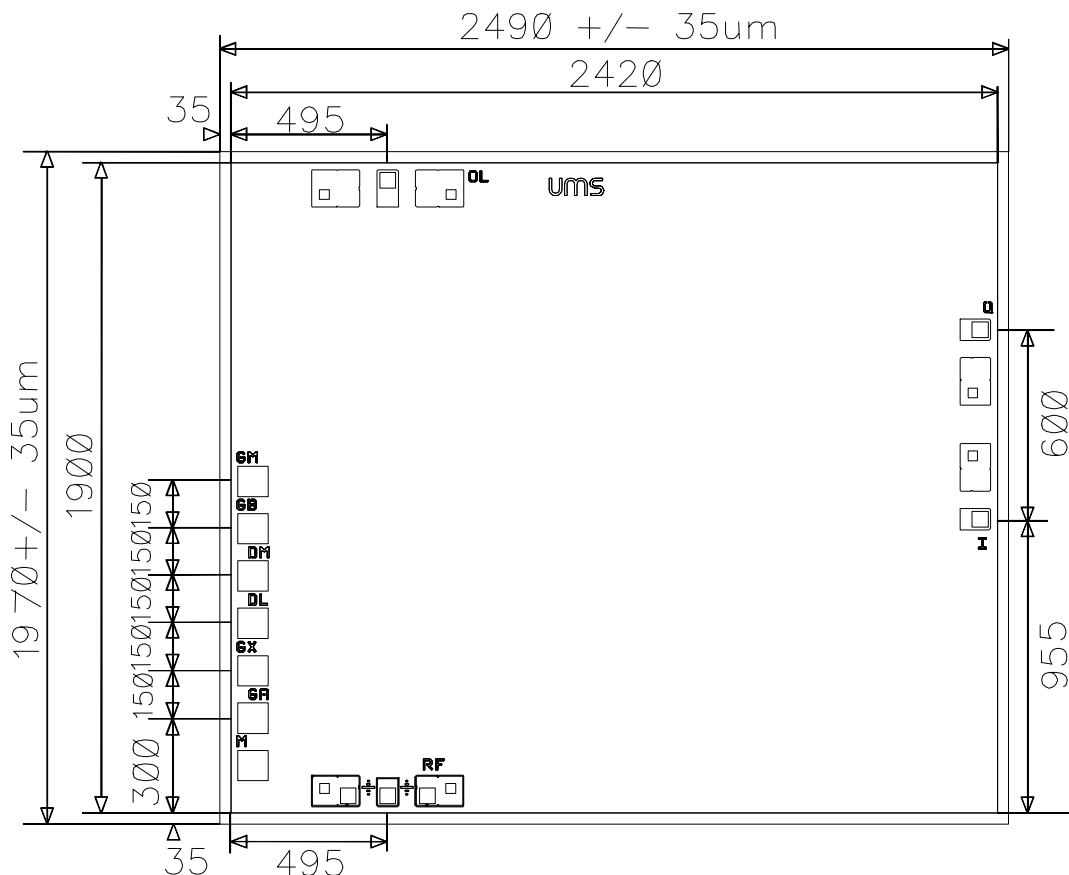


**Noise figure supradynic & infradyne versus IF frequency**

## Chip Assembly and Mechanical Data

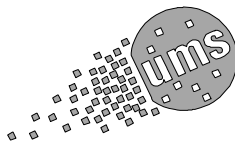


Note : Supply feed should be capacitively bypassed. 25µm diameter gold wire is recommended



### Bonding pad positions

( Chip thickness : 100µm. All dimensions are in micrometers )



## Ordering Information

Chip form : CHR2295-99F/00

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